

## BeSang Inc. announces 3D super-NAND flash memory

BeSang Inc., a pioneer in the monolithic 3-dimensional (3D) integrated circuits (IC), announced today its proprietary 3D super-NAND development.

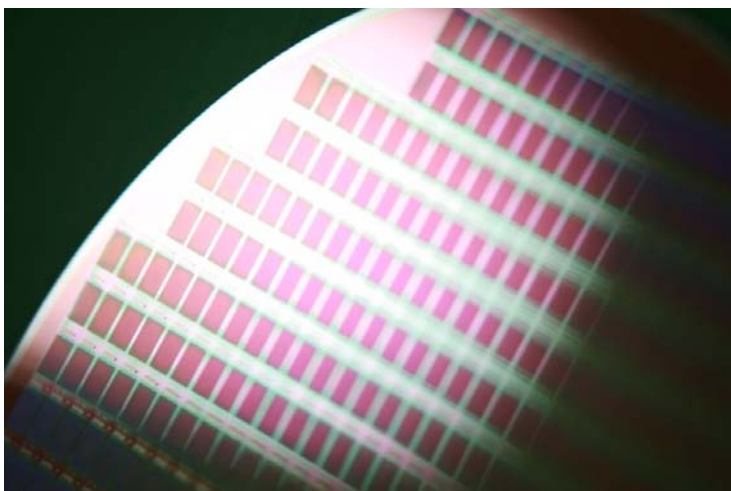
“We are pleased to announce 3D super-NAND which is expected to be the lowest ‘Cost-per-Bit’ in the NAND market,” said Dr. Sang-Yun Lee, founder and CEO of BeSang Inc. “For the first time in the semiconductor industry, 3D super-NAND brings parallel manufacturing process in order to achieve maximum productivity, where the parallel manufacturing means independent wafer processing of memory periphery logic at affordable old generation technology node and advanced 3D memory cells on top of the periphery.”

“Other 3D NAND has sequential manufacturing process to build stacked memory layers, staircase bit line contacts, and periphery logic. It takes usually more than 10 weeks to complete manufacturing process. However, 3D super-NAND takes only 5 days to complete advanced 3D non-volatile memory cells thanks to parallel manufacturing,” said Dr. Yohwan Koh, former senior vice president and head of NAND business at SK hynix, and recently joined advisor at BeSang Inc.

Compared to 48-layer 3D NAND, BeSang expects its 1-layer 3D super-NAND to have 5 to 10 times better ‘Cost-per-Bit.’ BeSang plans to bring 3D super-NAND to the market along with industry partners in 2016.

### About BeSang Inc.

BeSang is a pioneer in the design, development, and delivery of unsurpassed three-dimensional (3D) IC solutions, providing unmatched process and design technologies for TRUE 3D™ IC as well as technology licenses to customers. BeSang provides high-value intellectual properties related to its proprietary TRUE 3D™ ICs. The fabless semiconductor company is headquartered in Beaverton, Oregon, USA. Additional information is available at [www.besang.com](http://www.besang.com).



Picture: BeSang's proprietary 3D super-NAND flash memory